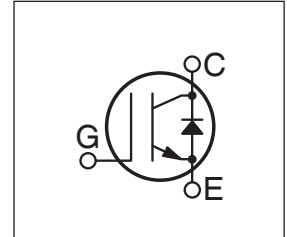
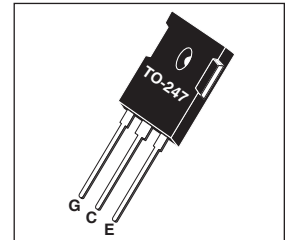


POWER MOS 7® IGBT

The POWER MOS 7® IGBT is a new generation of high voltage power IGBTs. Using Punch Through Technology this IGBT is ideal for many high frequency, high voltage switching applications and has been optimized for high frequency switchmode power supplies.

- **Low Conduction Loss** • **100 kHz operation @ 800V, 11A**
- **Low Gate Charge** • **50 kHz operation @ 800V, 19A**
- **Ultrafast Tail Current shutoff** • **RBSOA Rated**




MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

| Symbol | Parameter | APT25GP120BDQ1(G) | UNIT |
|----------------|---|-------------------|------------------|
| V_{CES} | Collector-Emitter Voltage | 1200 | Volts |
| V_{GE} | Gate-Emitter Voltage | ± 30 | |
| I_{C1} | Continuous Collector Current @ $T_C = 25^\circ\text{C}$ | 69 | Amps |
| I_{C2} | Continuous Collector Current @ $T_C = 110^\circ\text{C}$ | 33 | |
| I_{CM} | Pulsed Collector Current ^① @ $T_C = 150^\circ\text{C}$ | 90 | |
| RBSOA | Reverse Bias Safe Operating Area @ $T_j = 150^\circ\text{C}$ | 90A @ 960V | |
| P_D | Total Power Dissipation | 417 | Watts |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| T_L | Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec. | 300 | |

STATIC ELECTRICAL CHARACTERISTICS

| Symbol | Characteristic / Test Conditions | MIN | TYP | MAX | Units |
|---------------|---|------|-----|-----------|---------------|
| $V_{(BR)CES}$ | Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 350\mu\text{A}$) | 1200 | | | Volts |
| $V_{GE(TH)}$ | Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 1\text{mA}, T_j = 25^\circ\text{C}$) | 3 | 4.5 | 6 | |
| $V_{CE(ON)}$ | Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 25A, T_j = 25^\circ\text{C}$) | | 3.3 | 3.9 | |
| | Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 25A, T_j = 125^\circ\text{C}$) | | 3.0 | | |
| I_{CES} | Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_j = 25^\circ\text{C}$) ^② | | | 350 | μA |
| | Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_j = 125^\circ\text{C}$) ^② | | | 3000 | |
| I_{GES} | Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$) | | | ± 100 | nA |

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT25GP120BDQ1(G)

| Symbol | Characteristic | Test Conditions | MIN | TYP | MAX | UNIT | |
|--------------|---|---|------|------|-----|------|----|
| C_{ies} | Input Capacitance | Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$ | | 2090 | | pF | |
| C_{oes} | Output Capacitance | | | 200 | | | |
| C_{res} | Reverse Transfer Capacitance | | | 40 | | | |
| V_{GEP} | Gate-to-Emitter Plateau Voltage | Gate Charge | | 7.5 | | V | |
| Q_g | Total Gate Charge ⁽³⁾ | $V_{GE} = 15V$ | | 110 | | nC | |
| Q_{ge} | Gate-Emitter Charge | $V_{CE} = 600V$ | | 15 | | | |
| Q_{gc} | Gate-Collector ("Miller") Charge | $I_C = 25A$ | | 50 | | | |
| RBSOA | Reverse Bias Safe Operating Area | $T_J = 150^\circ\text{C}, R_G = 5\Omega, V_{GE} = 15V, L = 100\mu\text{H}, V_{CE} = 960V$ | 90 | | | A | |
| $t_{d(on)}$ | Turn-on Delay Time | Inductive Switching (25°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 25A$ $R_G = 5\Omega$ $T_J = +25^\circ\text{C}$ | | 12 | | ns | |
| t_r | Current Rise Time | | | 14 | | | |
| $t_{d(off)}$ | Turn-off Delay Time | | | 70 | | | |
| t_f | Current Fall Time | | | 39 | | | |
| E_{on1} | Turn-on Switching Energy ⁽⁴⁾ | | | 500 | | | μJ |
| E_{on2} | Turn-on Switching Energy (Diode) ⁽⁵⁾ | | 1090 | | | | |
| E_{off} | Turn-off Switching Energy ⁽⁶⁾ | | 440 | | | | |
| $t_{d(on)}$ | Turn-on Delay Time | Inductive Switching (125°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 25A$ $R_G = 5\Omega$ $T_J = +125^\circ\text{C}$ | | 12 | | ns | |
| t_r | Current Rise Time | | | 14 | | | |
| $t_{d(off)}$ | Turn-off Delay Time | | | 110 | | | |
| t_f | Current Fall Time | | | 90 | | | |
| E_{on1} | Turn-on Switching Energy ⁽⁴⁾ | | | 500 | | | μJ |
| E_{on2} | Turn-on Switching Energy (Diode) ⁽⁵⁾ | | | 1575 | | | |
| E_{off} | Turn-off Switching Energy ⁽⁶⁾ | | | 1185 | | | |

THERMAL AND MECHANICAL CHARACTERISTICS

| Symbol | Characteristic | MIN | TYP | MAX | UNIT |
|-----------------|--------------------------|-----|-----|------|------|
| $R_{\theta JC}$ | Junction to Case (IGBT) | | | .30 | °C/W |
| $R_{\theta JC}$ | Junction to Case (DIODE) | | | 1.18 | |
| W_T | Package Weight | | 5.9 | | gm |

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices, I_{ces} includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④ E_{on1} is the clamped inductive turn-on-energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. (See Figure 24.)

⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

APT Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT25GP120BDQ1(G)

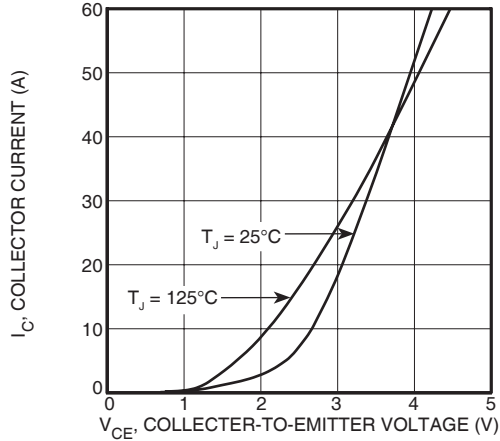


FIGURE 1, Output Characteristics(T_J = 25°C)

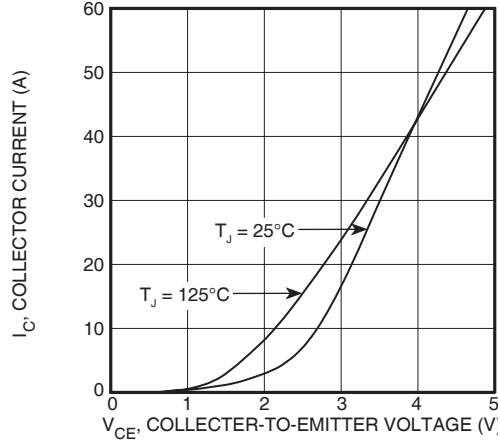


FIGURE 2, Output Characteristics (T_J = 125°C)

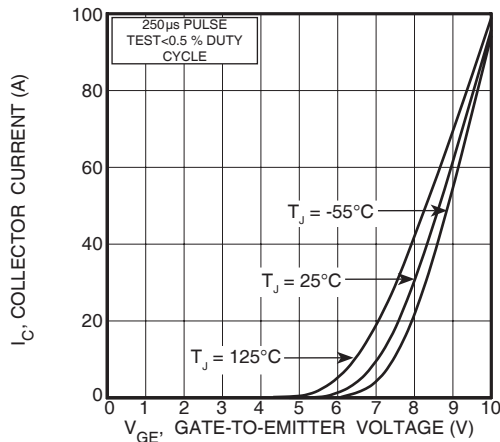


FIGURE 3, Transfer Characteristics

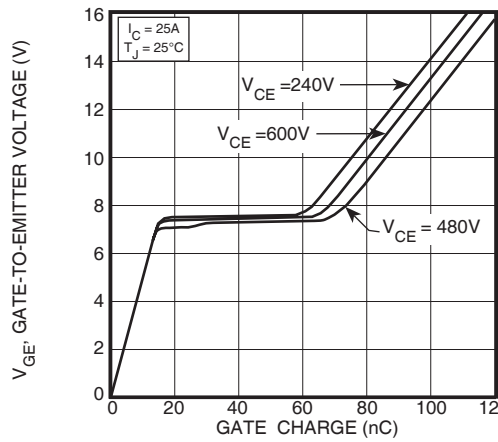


FIGURE 4, Gate Charge

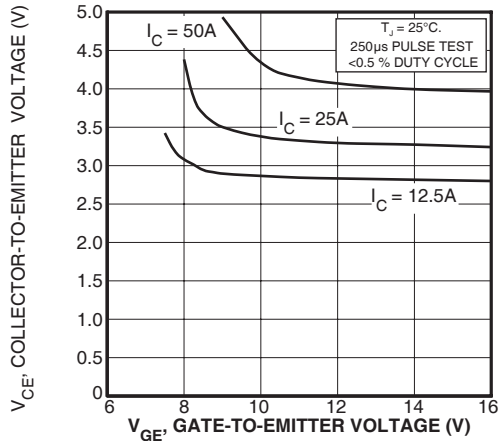


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

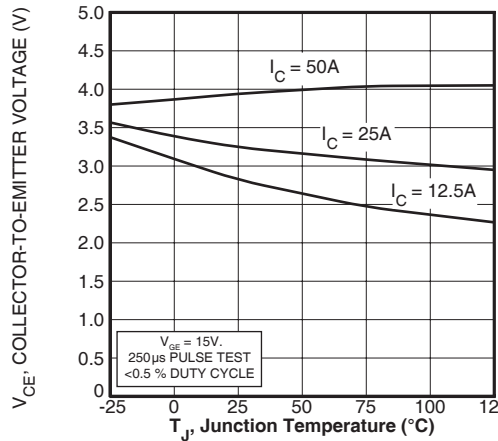


FIGURE 6, On State Voltage vs Junction Temperature

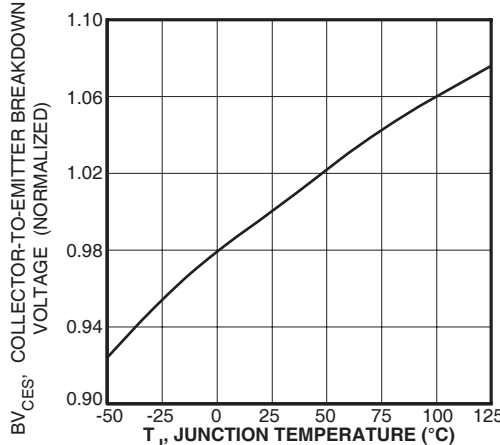


FIGURE 7, Breakdown Voltage vs. Junction Temperature

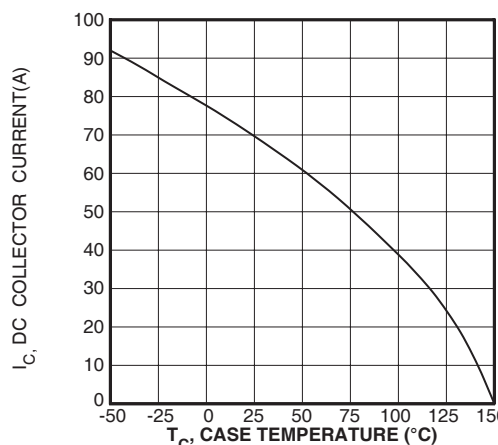


FIGURE 8, DC Collector Current vs Case Temperature

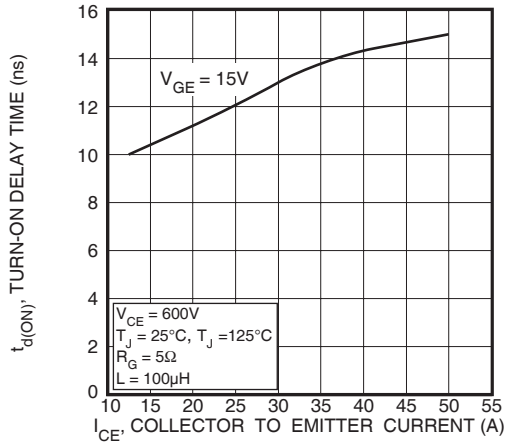


FIGURE 9, Turn-On Delay Time vs Collector Current

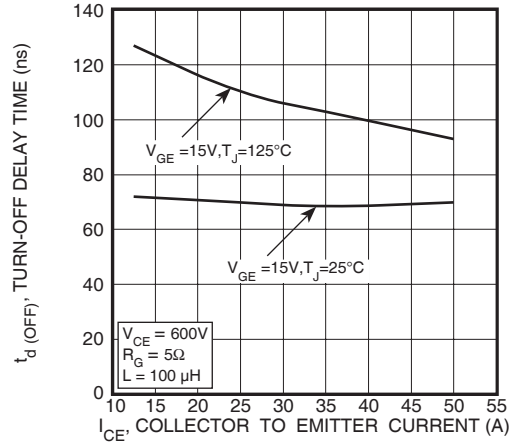


FIGURE 10, Turn-Off Delay Time vs Collector Current

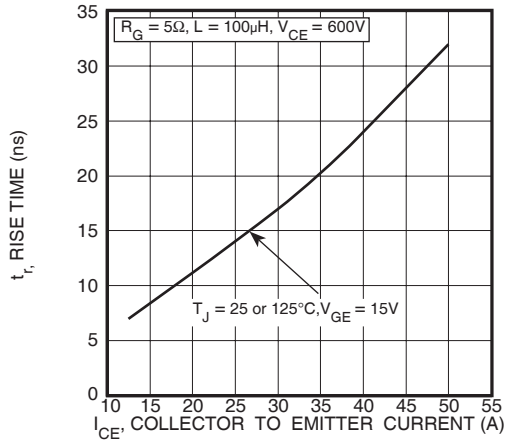


FIGURE 11, Current Rise Time vs Collector Current

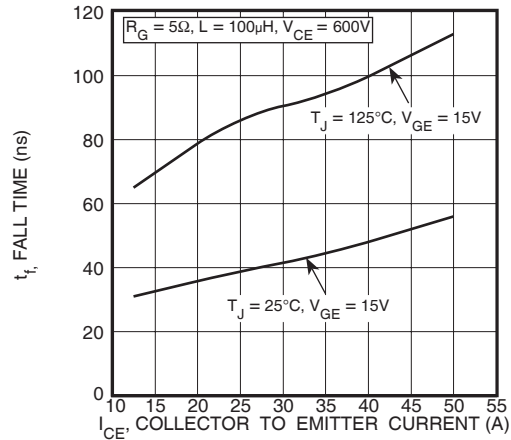


FIGURE 12, Current Fall Time vs Collector Current

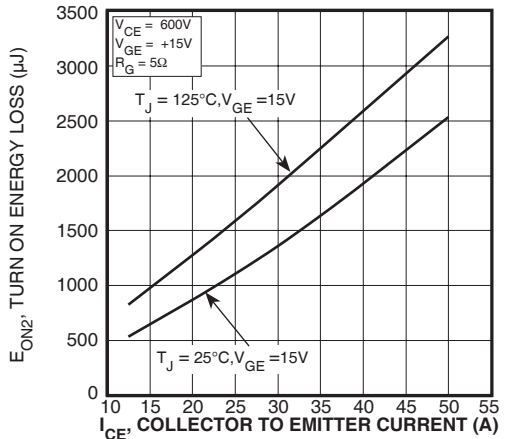


FIGURE 13, Turn-On Energy Loss vs Collector Current

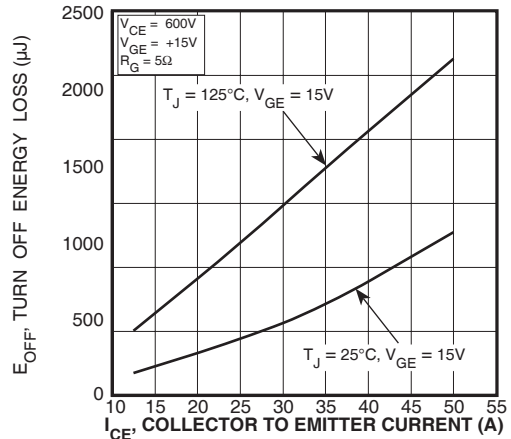


FIGURE 14, Turn Off Energy Loss vs Collector Current

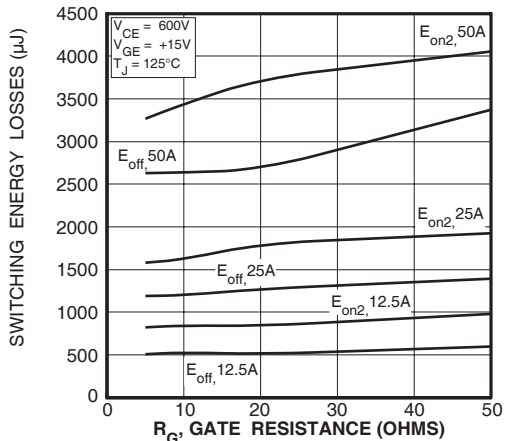


FIGURE 15, Switching Energy Losses vs. Gate Resistance

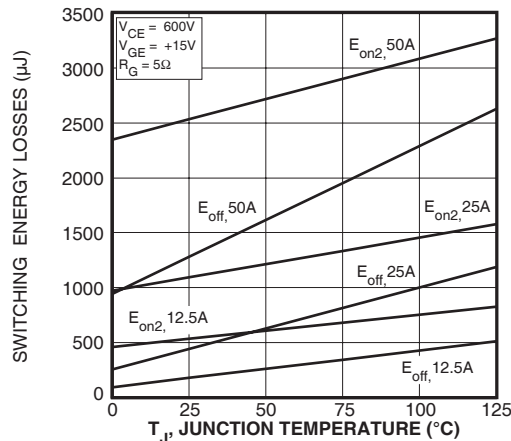


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

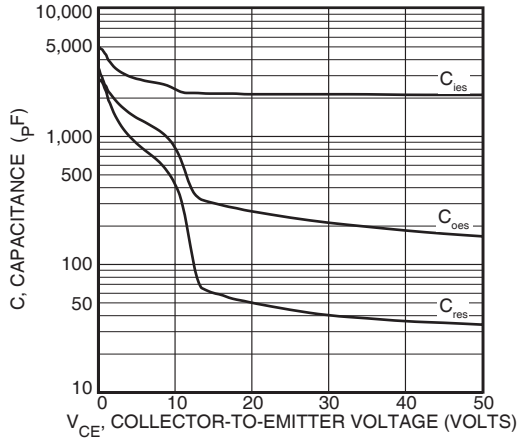


Figure 17, Capacitance vs Collector-To-Emitter Voltage

APT25GP120BDQ1(G)

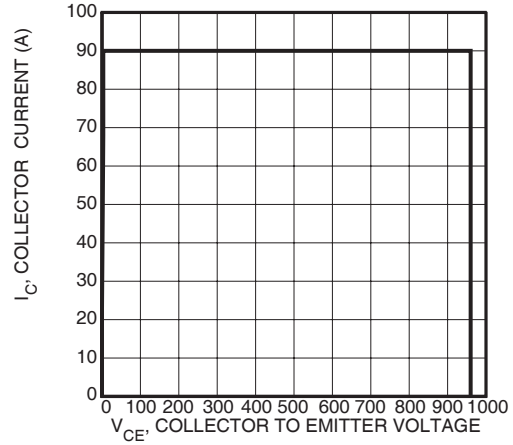


Figure 18, Minimum Switching Safe Operating Area

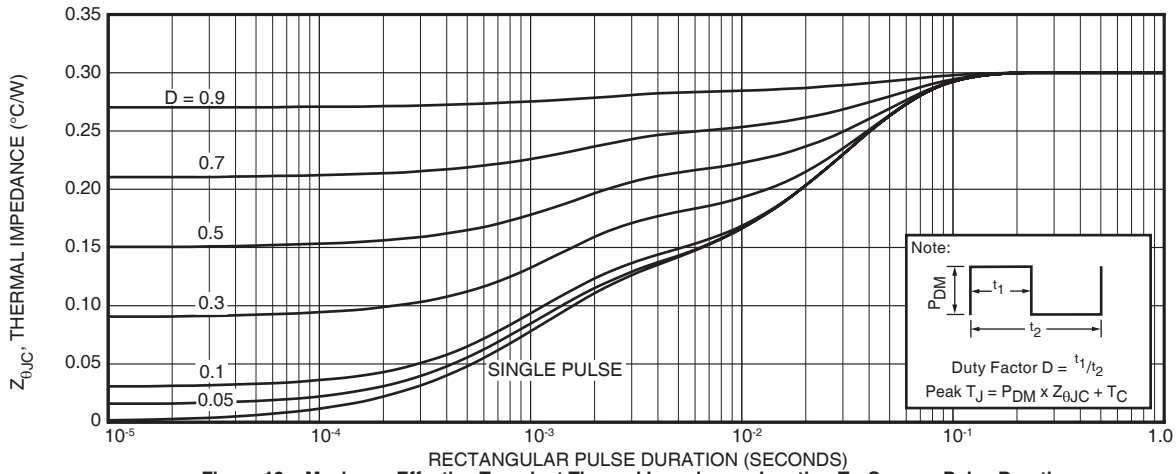


Figure 19a, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

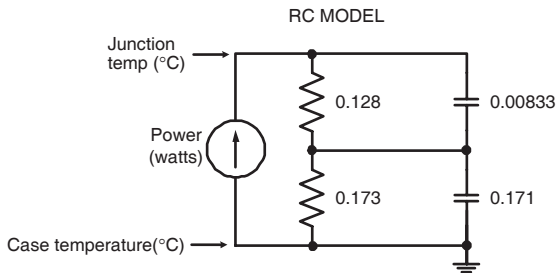


FIGURE 19b, TRANSIENT THERMAL IMPEDANCE MODEL

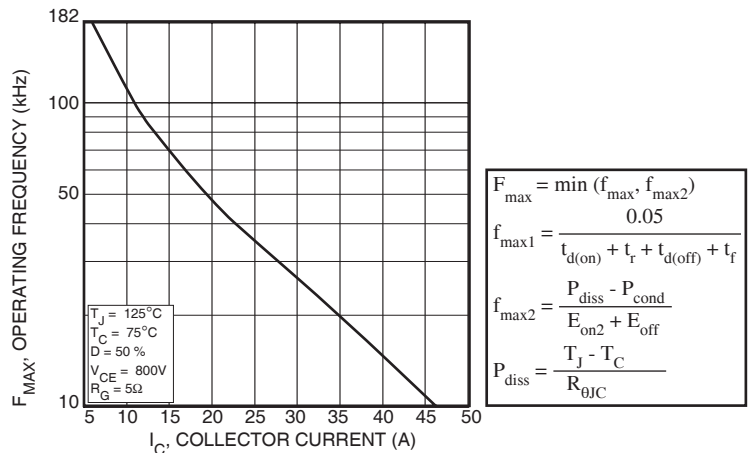


Figure 20, Operating Frequency vs Collector Current

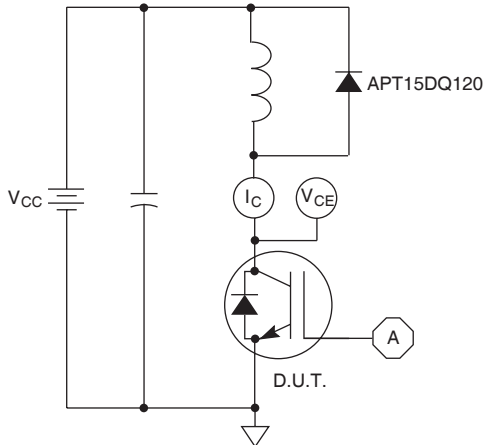


Figure 21, Inductive Switching Test Circuit

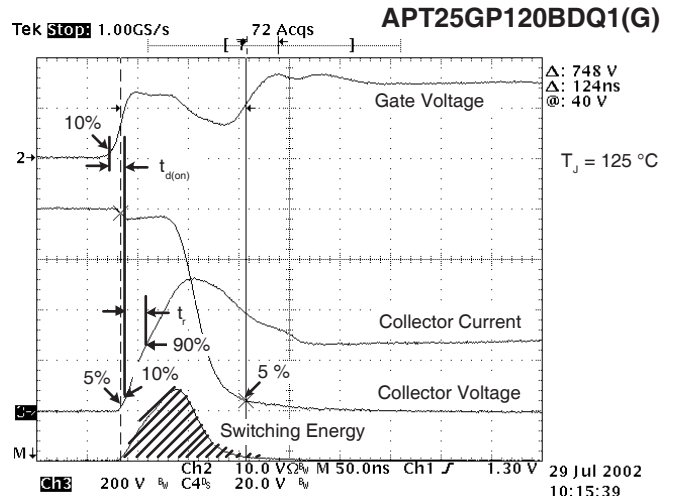


Figure 22, Turn-on Switching Waveforms and Definitions

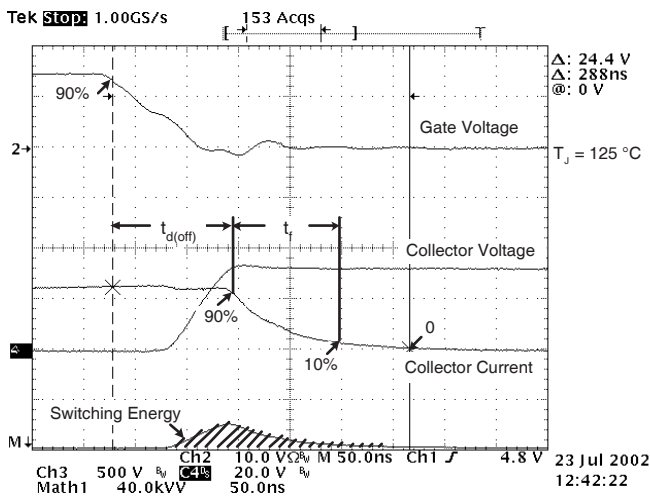


Figure 23, Turn-off Switching Waveforms and Definitions

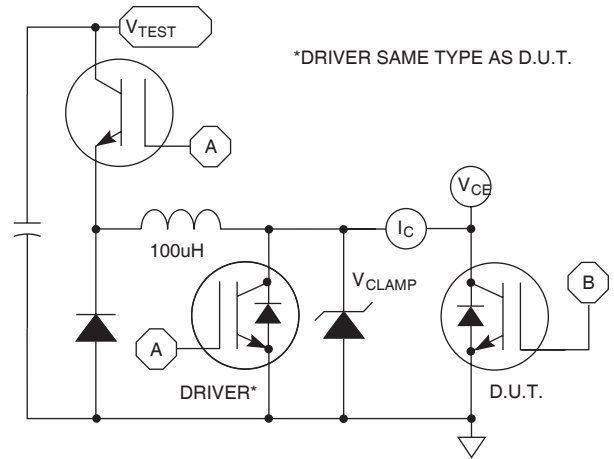


Figure 24, E_{ON1} Test Circuit

ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

| Symbol | Characteristic / Test Conditions | APT25GP120BDQ1(G) | | UNIT |
|------------|---|-------------------|-----|------|
| $I_F(AV)$ | Maximum Average Forward Current ($T_C = 127^\circ\text{C}$, Duty Cycle = 0.5) | | 15 | Amps |
| $I_F(RMS)$ | RMS Forward Current (Square wave, 50% duty) | | 29 | |
| I_{FSM} | Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms) | | 110 | |

STATIC ELECTRICAL CHARACTERISTICS

| Symbol | Characteristic / Test Conditions | MIN | TYP | MAX | UNIT |
|--------|----------------------------------|---|-----|------|-------|
| V_F | Forward Voltage | $I_F = 25\text{A}$ | | 3.24 | Volts |
| | | $I_F = 50\text{A}$ | | 4.03 | |
| | | $I_F = 25\text{A}, T_J = 125^\circ\text{C}$ | | 2.91 | |

DYNAMIC CHARACTERISTICS

| Symbol | Characteristic | Test Conditions | MIN | TYP | MAX | UNIT |
|-----------|----------------------------------|---|-----|------|-----|------|
| t_{rr} | Reverse Recovery Time | $I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$ | - | 21 | | ns |
| t_{rr} | Reverse Recovery Time | $I_F = 15\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 25^\circ\text{C}$ | - | 240 | | |
| Q_{rr} | Reverse Recovery Charge | | - | 260 | | nC |
| I_{RRM} | Maximum Reverse Recovery Current | | - | 3 | - | Amps |
| t_{rr} | Reverse Recovery Time | $I_F = 15\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 125^\circ\text{C}$ | - | 290 | | ns |
| Q_{rr} | Reverse Recovery Charge | | - | 960 | | nC |
| I_{RRM} | Maximum Reverse Recovery Current | | - | 6 | - | Amps |
| t_{rr} | Reverse Recovery Time | $I_F = 15\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 125^\circ\text{C}$ | - | 130 | | ns |
| Q_{rr} | Reverse Recovery Charge | | - | 1340 | | nC |
| I_{RRM} | Maximum Reverse Recovery Current | | - | 19 | | Amps |

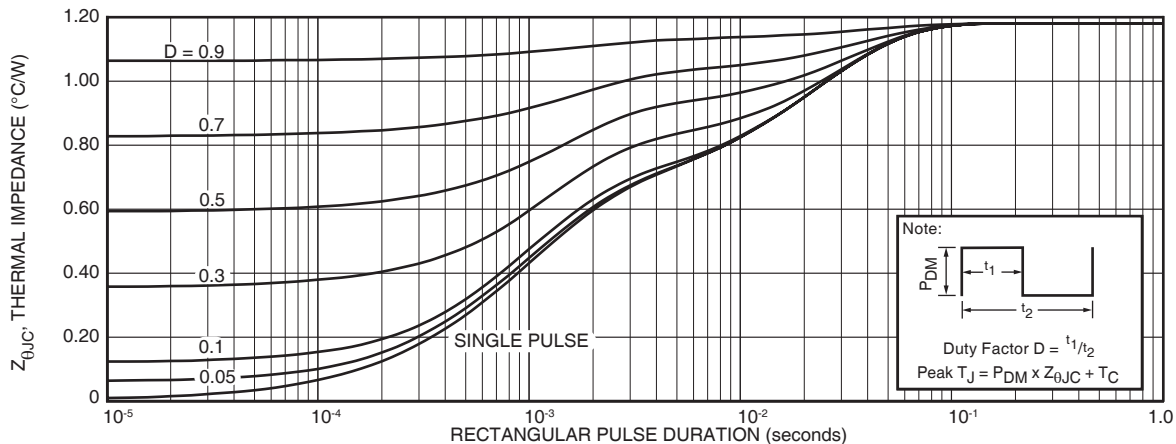


FIGURE 25a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION



FIGURE 25b. TRANSIENT THERMAL IMPEDANCE MODEL

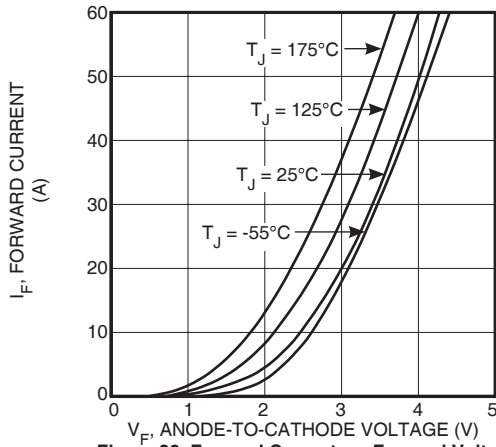


Figure 26. Forward Current vs. Forward Voltage

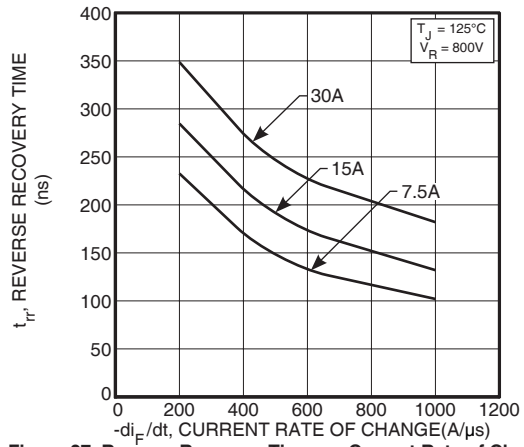


Figure 27. Reverse Recovery Time vs. Current Rate of Change

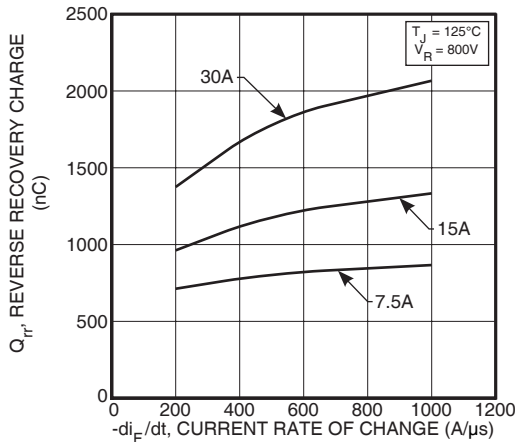


Figure 28. Reverse Recovery Charge vs. Current Rate of Change

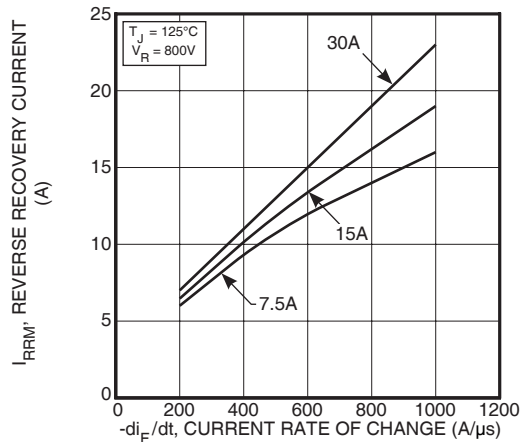


Figure 29. Reverse Recovery Current vs. Current Rate of Change



Figure 30. Dynamic Parameters vs. Junction Temperature



Figure 31. Maximum Average Forward Current vs. Case Temperature

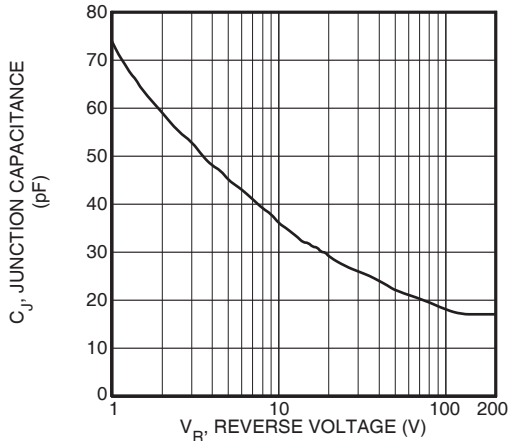


Figure 32. Junction Capacitance vs. Reverse Voltage

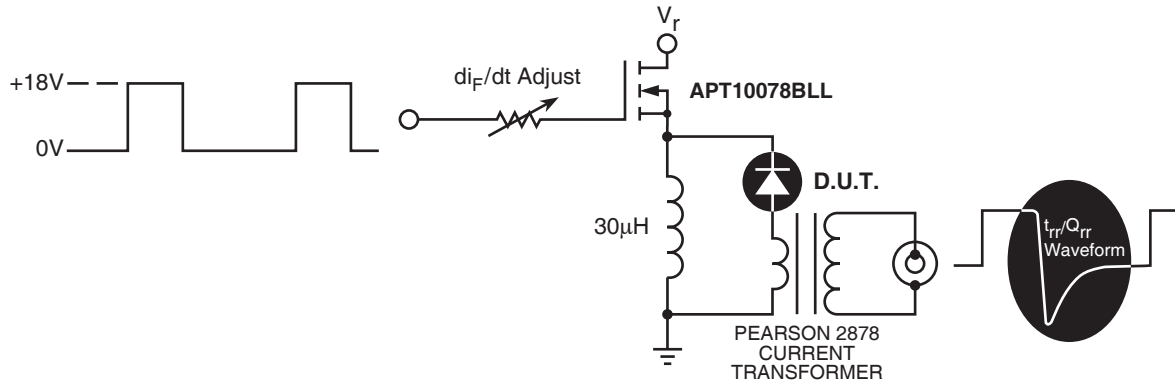


Figure 33. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

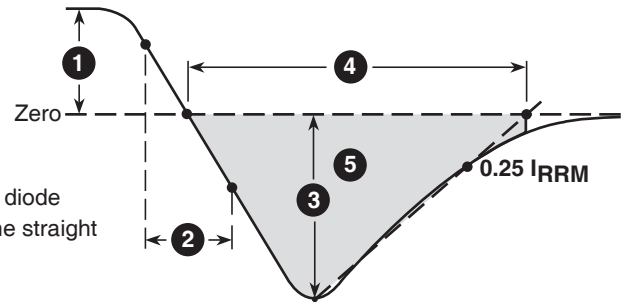
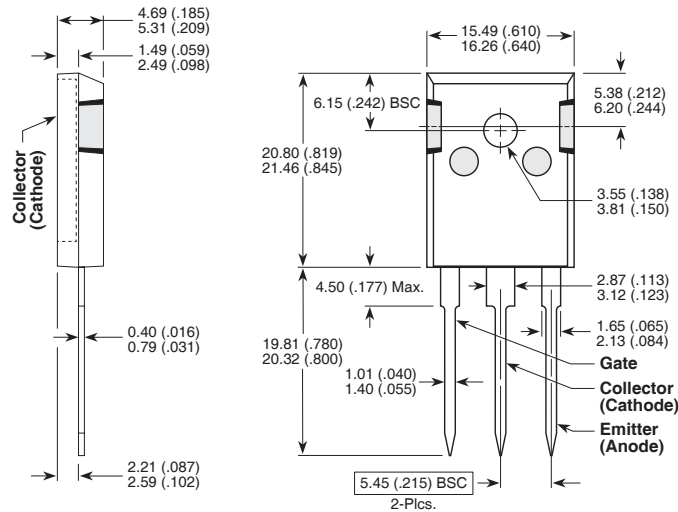


Figure 34, Diode Reverse Recovery Waveform and Definitions

TO-247 Package Outline

ⓔ1 SAC: Tin, Silver, Copper



Dimensions in Millimeters and (Inches)

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. US and Foreign patents pending. All Rights Reserved.



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Электрон
Связь**

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Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

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Электронная почта: sales@st-electron.ru

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Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331